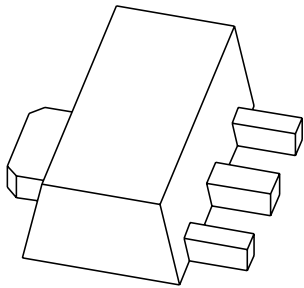


# DATA SHEET



## **BSR30; BSR31; BSR33** PNP medium power transistors

Product data sheet  
Supersedes data of 1999 Apr 26

2004 Dec 13

# PNP medium power transistors

# BSR30; BSR31; BSR33

### FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

### APPLICATIONS

- Telephony and general industrial applications
- Thick and thin-film circuits.

### DESCRIPTION

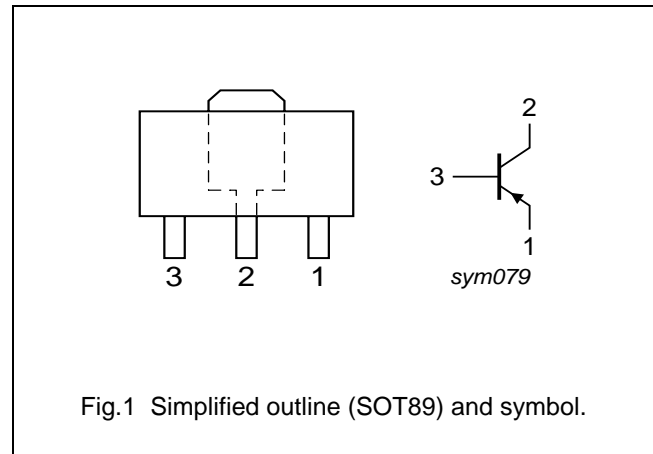
PNP medium power transistor in a SOT89 plastic package.  
NPN complements: BSR40; BSR41 and BSR43.

### MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| BSR30       | BR1          |
| BSR31       | BR2          |
| BSR33       | BR4          |

### PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | emitter     |
| 2   | collector   |
| 3   | base        |



### ORDERING INFORMATION

| TYPE NUMBER | PACKAGE |  |         |
|-------------|---------|--|---------|
|             | NAME    | DESCRIPTION  | VERSION |
| BSR30       | SC-62   | plastic surface mounted package; collector pad for good heat transfer; 3 leads | SOT89   |
| BSR31       |         |  |         |
| BSR33       |         |  |         |

## PNP medium power transistors

## BSR30; BSR31; BSR33

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                 | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|---------------------------|----------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                     |      |      |      |
|                  | BSR30; BSR31              |                                  | –    | –70  | V    |
|                  | BSR33                     |                                  | –    | –90  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                        |      |      |      |
|                  | BSR30; BSR31              |                                  | –    | –60  | V    |
|                  | BSR33                     |                                  | –    | –80  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                   | –    | –5   | V    |
| I <sub>C</sub>   | collector current (DC)    |                                  | –    | –1   | A    |
| I <sub>CM</sub>  | peak collector current    |                                  | –    | –2   | A    |
| I <sub>BM</sub>  | peak base current         |                                  | –    | –200 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C; note 1 | –    | 1.35 | W    |
| T <sub>stg</sub> | storage temperature       |                                  | –65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature      |                                  | –    | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                  | –65  | +150 | °C   |

**Note**

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.  
For other mounting conditions, see *“Thermal considerations for SOT89 in the General Part of associated Handbook”*.

**THERMAL CHARACTERISTICS**

| SYMBOL               | PARAMETER   | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient         | note 1     | 93    | K/W  |
| R <sub>th(j-s)</sub> | thermal resistance from junction to soldering point |            | 13    | K/W  |

**Note**

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.  
For other mounting conditions, see *“Thermal considerations for SOT89 in the General Part of associated Handbook”*.

## PNP medium power transistors

## BSR30; BSR31; BSR33

**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

| SYMBOL      | PARAMETER                            | CONDITIONS  | MIN. | MAX.  | UNIT          |
|-------------|--------------------------------------|---|------|-------|---------------|
| $I_{CBO}$   | collector-base cut-off current       | $I_E = 0\text{ A}; V_{CB} = -60\text{ V}$                             | –    | –100  | nA            |
|             |                                      | $I_E = 0\text{ A}; V_{CB} = -60\text{ V}; T_j = 150\text{ °C}$        | –    | –50   | $\mu\text{A}$ |
| $I_{EBO}$   | emitter-base cut-off current         | $I_C = 0\text{ A}; V_{EB} = -5\text{ V}$                              | –    | –100  | nA            |
| $h_{FE}$    | DC current gain                      | $I_C = -100\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; \text{note 1}$  | 10   | –     |               |
|             | BSR30                                |   |      |       |               |
|             | BSR31; BSR33                         | 30  | –    |       |               |
|             | DC current gain                      | $I_C = -100\text{ mA}; V_{CE} = -5\text{ V}; \text{note 1}$           | 40   | 120   |               |
|             | BSR30                                |   |      |       |               |
|             | BSR31; BSR33                         | 100   | 300  |       |               |
|             | DC current gain                      | $I_C = -500\text{ mA}; V_{CE} = -5\text{ V}; \text{note 1}$           | 30   | –     |               |
|             | BSR30                                |   |      |       |               |
|             | BSR31; BSR33                         | 50  | –    |       |               |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C = -150\text{ mA}; I_B = -15\text{ mA}; \text{note 1}$            | –    | –0.25 | V             |
|             |                                      | $I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$            | –    | –0.5  | V             |
| $V_{BEsat}$ | base-emitter saturation voltage      | $I_C = -150\text{ mA}; I_B = -15\text{ mA}; \text{note 1}$            | –    | –1    | V             |
|             |                                      | $I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$            | –    | –1.2  | V             |
| $f_T$       | transition frequency                 | $I_C = -50\text{ mA}; V_{CE} = -10\text{ V};$<br>$f = 100\text{ MHz}$ | 100  | –     | MHz           |

**Note**

1. Pulse test:  $t_p = 300\text{ }\mu\text{s}; \delta < 0.01$ .

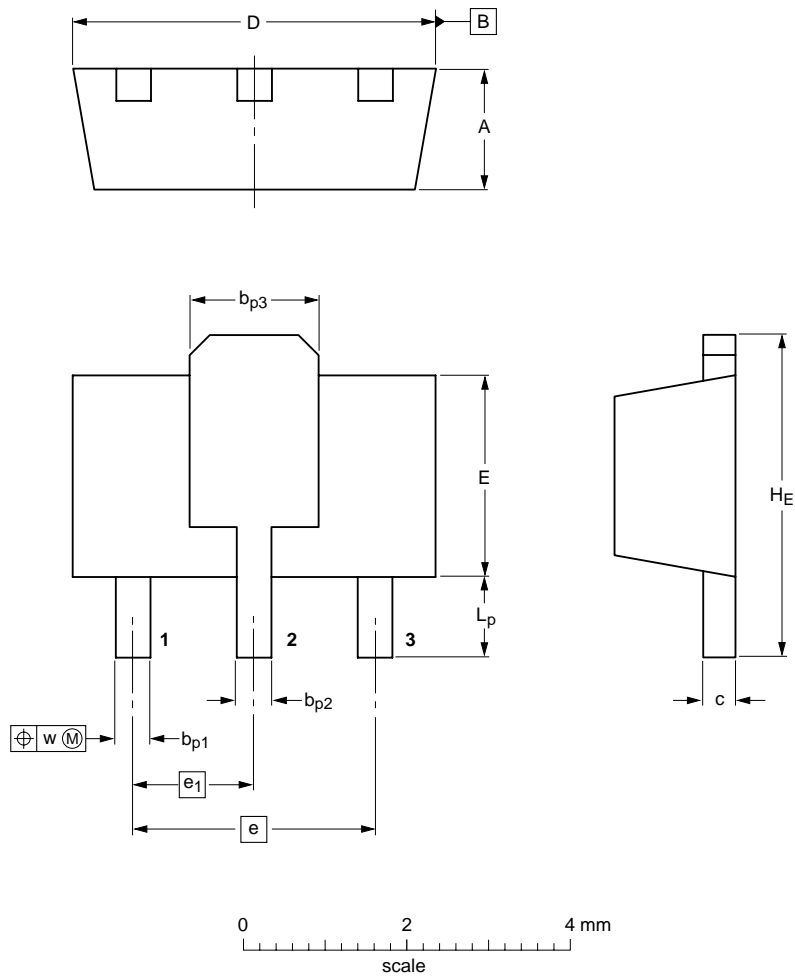
PNP medium power transistors

BSR30; BSR31; BSR33

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | b <sub>p1</sub> | b <sub>p2</sub> | b <sub>p3</sub> | c            | D          | E          | e   | e <sub>1</sub> | H <sub>E</sub> | L <sub>p</sub> | w    |
|------|------------|-----------------|-----------------|-----------------|--------------|------------|------------|-----|----------------|----------------|----------------|------|
| mm   | 1.6<br>1.4 | 0.48<br>0.35    | 0.53<br>0.40    | 1.8<br>1.4      | 0.44<br>0.23 | 4.6<br>4.4 | 2.6<br>2.4 | 3.0 | 1.5            | 4.25<br>3.75   | 1.2<br>0.8     | 0.13 |

| OUTLINE VERSION | REFERENCES |        |       |  | EUROPEAN PROJECTION | ISSUE DATE           |
|-----------------|------------|--------|-------|--|---------------------|----------------------|
|                 | IEC        | JEDEC  | JEITA |  |                     |                      |
| SOT89           |            | TO-243 | SC-62 |  |                     | 04-08-03<br>06-03-16 |

PNP medium power transistors

BSR30; BSR31; BSR33

**DATA SHEET STATUS**

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION  |
|--------------------------------|-------------------------------|---|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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